



PJQ4464AP

60V N-Channel Enhancement Mode MOSFET

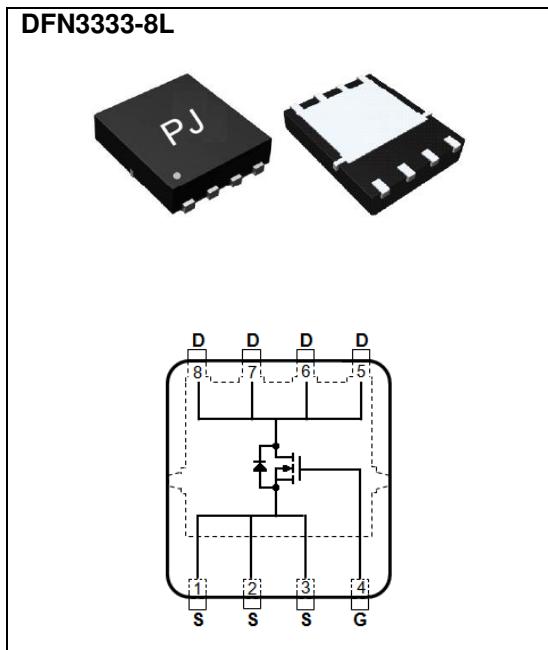
Voltage 60 V Current 33 A

Features

- $R_{DS(ON)}$, $V_{GS}=10V$, $I_D=16A < 17m\Omega$
- $R_{DS(ON)}$, $V_{GS}=4.5V$, $I_D=8A < 20m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0002 ounces, 0.006 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^(Note 4)	I_D	33	A
		21	
Pulsed Drain Current ^(Note 1)	I_{DM}	132	W
Power Dissipation	P_D	40	
		16	A
Continuous Drain Current	I_D	7.3	W
		5.9	
Power Dissipation	P_D	2.0	$^\circ C/W$
		1.3	
Single Pulse Avalanche Energy ^(Note 6)	E_{AS}	45	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ C$
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	3.1	$^\circ C/W$
	Junction to Ambient	62.5	

- Limited only by Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.7	2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=16A$	-	13	17	$m\Omega$
		$V_{GS}=4.5V, I_D=8A$	-	16	20	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Dynamic ^(Note 5)						
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=10A,$ $V_{GS}=4.5V$ ^(Note 1,2)	-	13.5	-	nC
Gate-Source Charge	Q_{gs}		-	4.8	-	
Gate-Drain Charge	Q_{gd}		-	4.9	-	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $f=1MHz$	-	1574	-	pF
Output Capacitance	C_{oss}		-	118	-	
Reverse Transfer Capacitance	C_{rss}		-	77	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=1A,$ $V_{GS}=10V, R_G=6\Omega$ ^(Note 1,2)	-	11	-	ns
Turn-On Rise Time	t_r		-	11	-	
Turn-Off Delay Time	$t_{d(off)}$		-	35	-	
Turn-Off Fall Time	t_f		-	8.1	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	33	A
Reverse Recovery Time	V_{SD}	$I_S=1A, V_{GS}=0V$	-	0.68	1	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ C$. Ratings are based on low frequency and duty cycles to keep initial $T_J = 25^\circ C$.
4. The maximum current rating is package limited.
5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. The test condition is $L=0.1mH, I_{AS}=30A, V_{DD}=25V, V_{GS}=10V$, Starting $T_J=25^\circ C$.
7. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

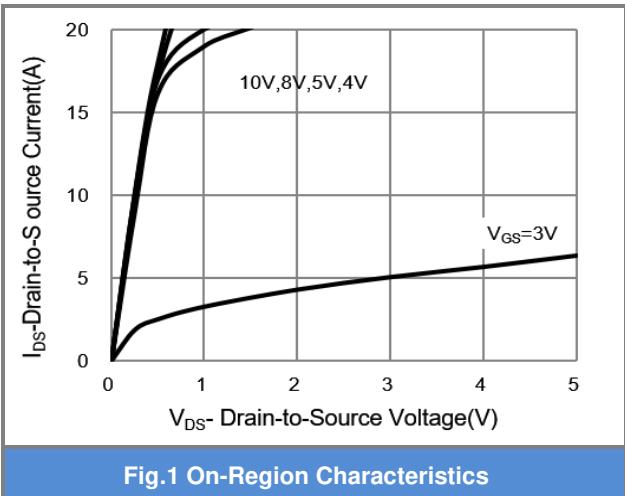


Fig.1 On-Region Characteristics

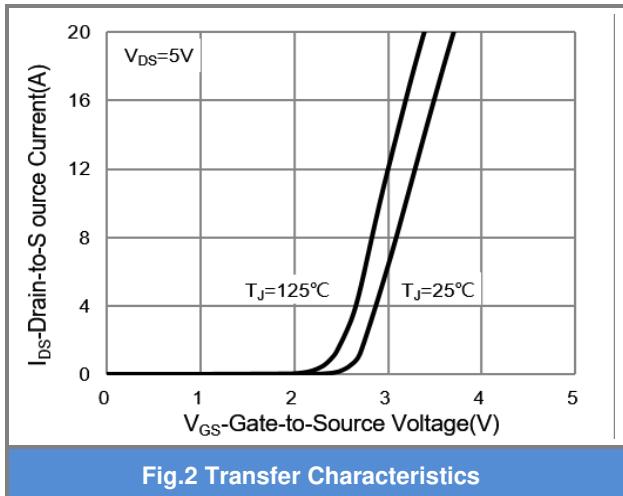


Fig.2 Transfer Characteristics

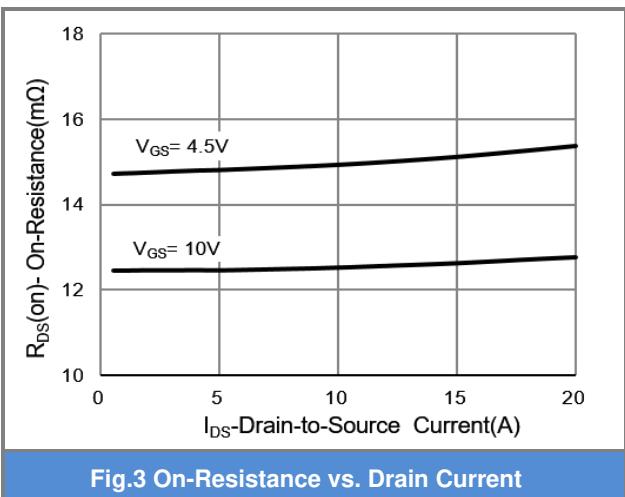


Fig.3 On-Resistance vs. Drain Current

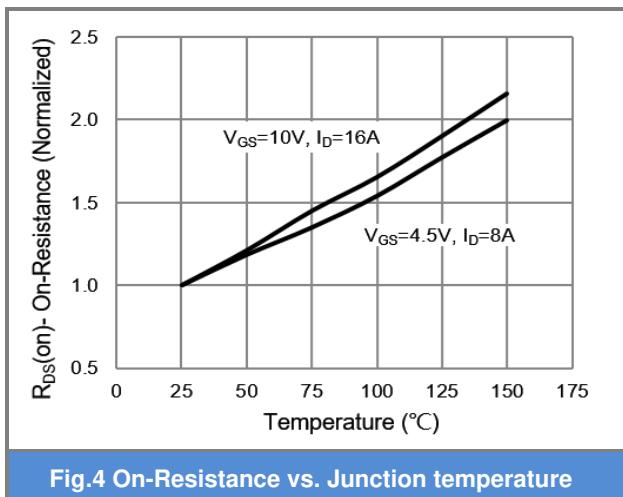


Fig.4 On-Resistance vs. Junction temperature

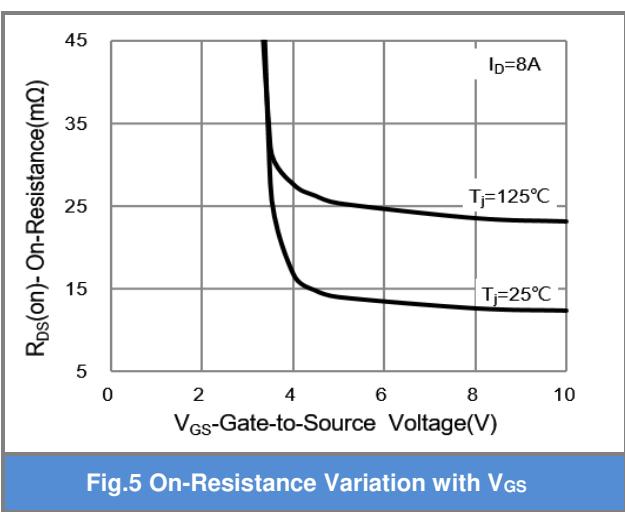


Fig.5 On-Resistance Variation with V_GS

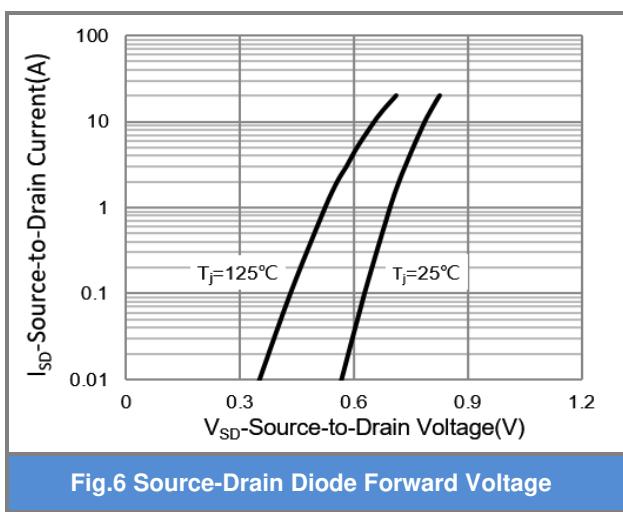


Fig.6 Source-Drain Diode Forward Voltage



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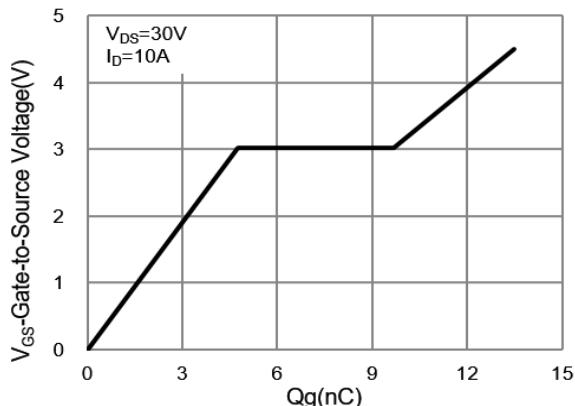


Fig.7 Gate-Charge Characteristics

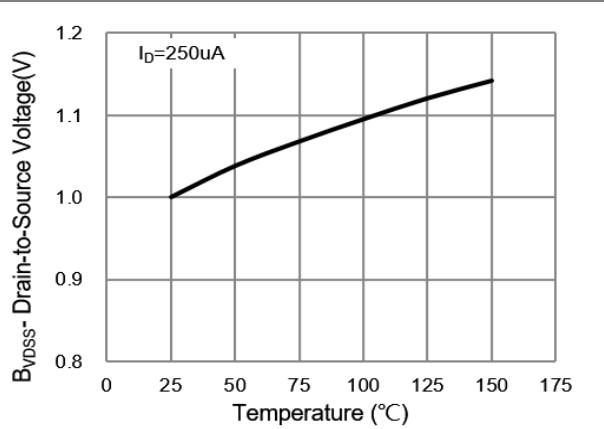


Fig.8 Breakdown Voltage Variation vs. Temperature

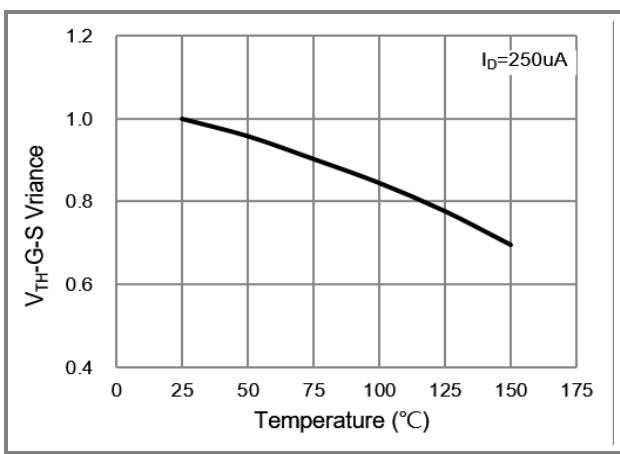


Fig.9 Threshold Voltage Variation with Temperature

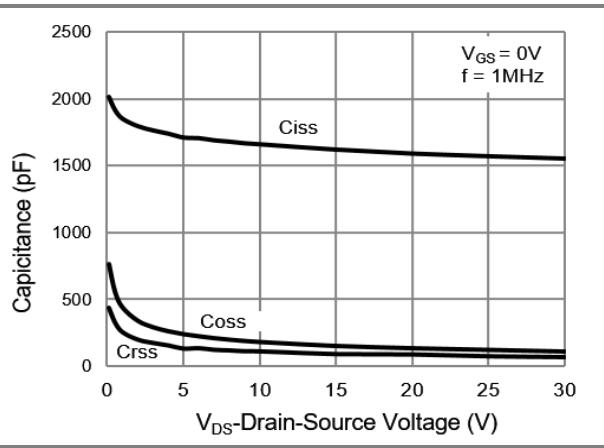


Fig.10 Capacitance vs. Drain-Source Voltage

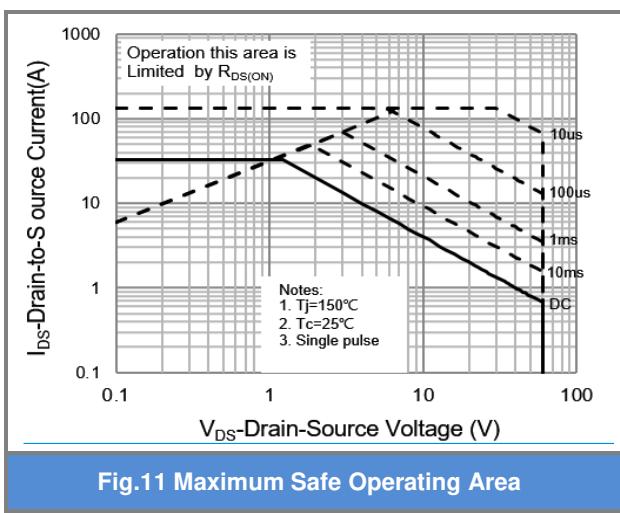
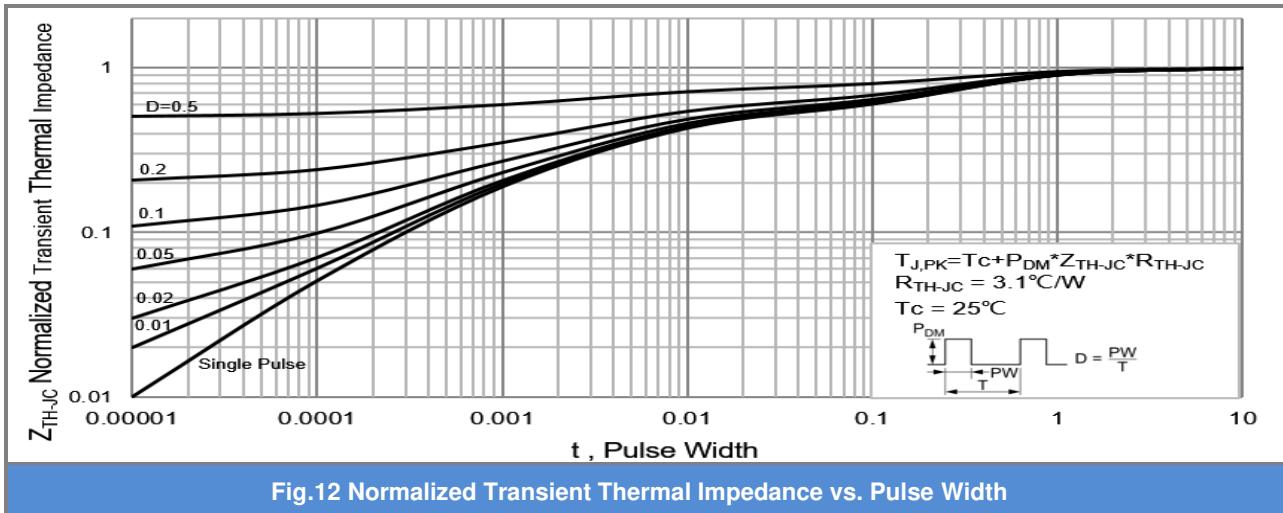


Fig.11 Maximum Safe Operating Area



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TYPICAL CHARACTERISTIC CURVES



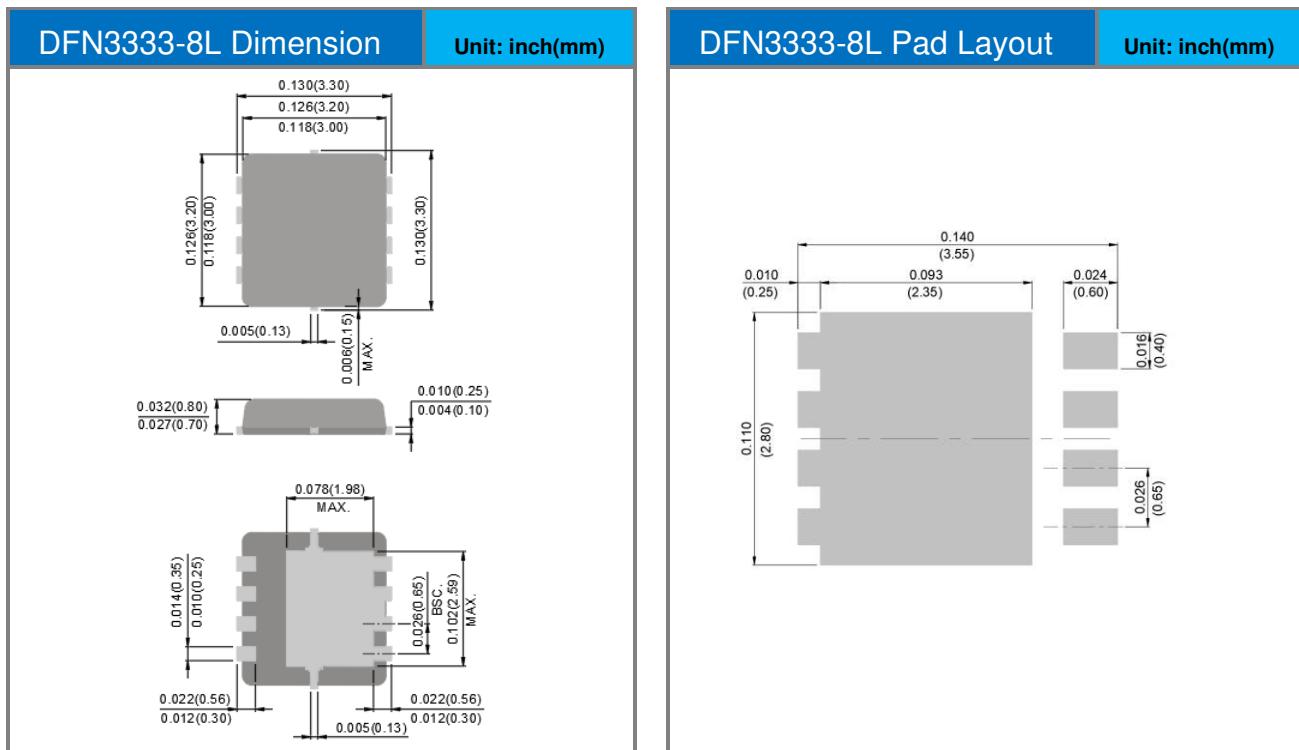


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Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4464AP_R2_00001	DFN3333-8L	5K pcs / 13" reel	4464	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout





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